

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete if Known

Application Number	09/945500
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 1 of 2

Attorney Docket No: 01303.029US1

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LP	US-4780424	10/25/1988	Holler, Mark A	437	29	09/28/1987
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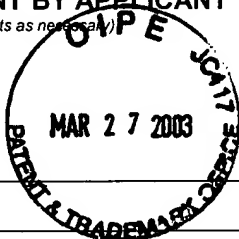
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Application Number	09/945500
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First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Pham, Ly

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Attorney Docket No: 1303.029US1

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LP	US-6,124,729	09/26/2000	Noble, W. P., et al.	326	41	02/27/1998
LP	US-6,134,175	10/17/2000	Forbes, L., et al.	365	230.06	08/04/1998
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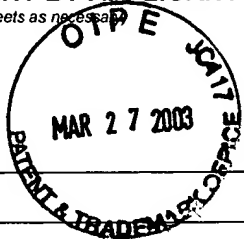
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Sheet 2 of 3

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Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Pham, Ly

Attorney Docket No: 1303.029US1

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Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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